Monika Bhattacharya

List of Publications by Year
in descending order

17	98	1684188 5	1474206 9
papers	citations	h-index	g-index

17	17	17	59
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	An Accurate Charge-Control-Based Approach for Noise Performance Assessment of a Symmetric Tied-Gate InAlAs/InGaAs DG-HEMT. IEEE Transactions on Electron Devices, 2012, 59, 1644-1652.	3.0	17
2	Scattering parameter based modeling and simulation of symmetric tied-gate InAlAs/InGaAs DG-HEMT for millimeter-wave applications. Solid-State Electronics, 2011, 63, 149-153.	1.4	12
3	Polarization dependent charge control model for microwave performance assessment of AlGaN/GaN/AlGaN double heterostructure HEMTs. Journal of Computational Electronics, 2018, 17, 1229-1240.	2.5	12
4	Impact of doping concentration and donor-layer thickness on the dc characterization of symmetric double-gate and single-gate InAlAs/InGaAs/InP HEMT for nanometer gate dimension-A comparison. , 2010, , .		9
5	Temperature-Dependent Analytical Model for Microwave and Noise Performance Characterization of $hbox{In}_{0.52}hbox{Al}_{0.48}hbox{As/In}_{m} hbox{Ga}_{1-m}hbox{As}$$(hbox{0.53} leq m leq) Tj ETQq1 1 0.784314 rgBT /Ov	1.0	8
6	Sheet carrier concentration and currentâ€“voltage analysis of Al0.15Ga0.85N/GaN/Al0.15Ga0.85N double heterostructure hemt incorporating the effect of traps. Microsystem Technologies, 2022, 28, 665-674.	2.0	8
7	Applicability of Field Plate in Double Channel GaN HEMT for Radio-Frequency and Power-Electronic Applications. Silicon, 0, , 1.	3.3	8
8	Sheet carrier concentration and threshold voltage modeling of asymmetrically doped AlGaN/GaN/AlGaN double heterostructure HEMT. , 2017, , .		7
9	Analysis of Al0.15Ga0.85N/GaN/Al0.15Ga0.85N DH-HEMT for RF and Microwave Frequency Applications. Semiconductors, 2019, 53, 1784-1791.	0.5	5
10	Impact of Temperature and Indium Composition in the Channel on the Microwave Performance of Single-Gate and Double-Gate InAlAs/InGaAs HEMT. IEEE Nanotechnology Magazine, 2013, 12, 965-970.	2.0	4
11	Extraction of admittance parameters of symmetrically doped AlGaN/GaN/AlGaN DH-HEMT for microwave frequency applications. Microsystem Technologies, 2021, 27, 4065-4072.	2.0	4
12	Influence of gate leakage current induced shot noise on the Minimum Noise FigureÂof InAlAs/InGaAs double-gate HEMT. Superlattices and Microstructures, 2017, 109, 13-22.	3.1	3
13	Impact of Donor Layer Thickness, Doping Concentration and Gate-Width on Gate-Capacitance of AlGaN/GaN Single and Double Heterostructure HEMT for Microwave Frequency Applications. , 2018, , .		1
14	A comprehensive charge control based analysis of the effect of donor-layer doping and donor-layer thickness on the P, R and C noise coefficients of a symmetric tied-gate InAlAs/InGaAs DG-HEMT. Proceedings of SPIE, 2012, , .	0.8	0
15	Impact of noise temperature constant and diffusion coefficient on the minimum noise figure and minimum noise temperature of InAlAs/InGaAs DGHEMT. , 2012, , .		0
16	RF Performance comparison of Dual Material Gate (DMG) and Conventional AlGaN/GaN High Electron Mobility Transistor. , 2018, , .		0
17	Impact of donor-layer doping & thickness, gate-length and temperature on potential and electron concentration in AlGaN/GaN Double-Heterostructure and Single-Heterostructure HEMT. , 2018, , .		0